

12. (Previously Added) The photoelectric conversion element according to claim 10, wherein a p^+ layer is provided between the p^- layer and the electrode, and the electrode is in contact with the n^+ layer.

REMARKS

The only claims in the application, Claims 7, 9, 10, and 12, were rejected under 35 U.S.C. § 102(b) as being anticipated by the cited Takebe reference (Claims 7 and 9) and by the cited Miyabayashi patent (Claims 10 and 12), and all but Claim 12 were rejected under 35 U.S.C. § 112.

Referring first to the rejections under 35 U.S.C. § 112, the antecedent basis issues raised by the Examiner have been addressed and remedied.

With regard to the rejections based on prior art, Applicants respectfully submit that the revised language of the claims defines the invention in terms which are patentably distinct from Takebe and Miyabayashi references. Particularly, independent Claim 7 specifies that an active layer of single-crystal silicon has a (111) plane as its surface, wherein an angle θ , defined by any arbitrary two cutting lines on the surface, which do not come into coincidence, corresponds to $|\cos\theta| = \frac{1}{2}$ or $3^{1/2}/2$. Applicants assert that Takebe does not disclose the single-crystal silicon or the cutting line relationship of Claim 7. Accordingly, Claim 7 and its dependent Claim 9 are believed to be allowable.

Independent Claim 10 defines the p^+ and p^- layers of a photoelectric conversion element as being silicon-crystal, with the p^- layer having a thickness of about 30 μm . Also, any surface deviation of the surface of the (111) plane are required to be within an angle of 24/60ths

of a degree, thereby providing an advantage of a very slight stacking fault density. This structure is not disclosed by Miyabayashi, wherefore Claim 10, as well as its dependent claim 12, is believed to be allowable.

For all of these various reasons Applicants respectfully request issuance of a formal Notice of Allowance.

Applicants' undersigned attorney may be reached in our New York office by telephone at (212) 218-2100. All correspondence should continue to be directed to our below listed address.

Respectfully submitted,



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